SOOS032-D3908, FEBRUARY 1992

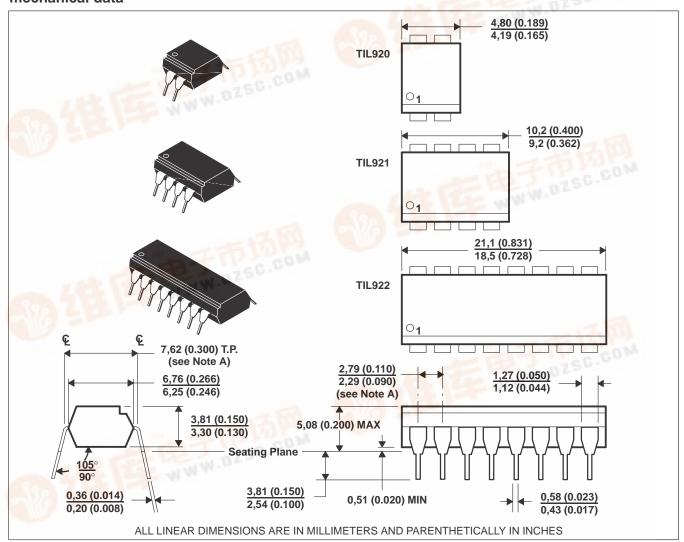
- AC Signal Input
- Gallium-Arsenide Diode Infrared Source
- Source Is Optically Coupled to Silicon N-P-N Phototransistor
- Choice of One, Two, or Four Channels

- Choice of Three Current-Transfer Ratios
- High-Voltage Electrical Isolation . . . 7.5 kV
  Peak (5.3 kV rms)
- Plastic Dual-In-Line Packages
- UL Listed File No. E65085

### description

These optocouplers consist of two gallium-arsenide light-emitting diodes connected in a reverse-parallel configuration for ac-input applications and a silicon n-p-n phototransistor per channel. The TIL920 has one channel in a 4-pin package, the TIL921 has two channels in an 8-pin package, and the TIL922 has four channels in a 16-pin package. The standard devices, TIL920, TIL921, and TIL922, are tested for a current-transfer ratio of 20% minimum. Devices selected for a current-transfer ratio of 50% and 100% minimum are designated with the suffix A and B respectively.

#### mechanical data

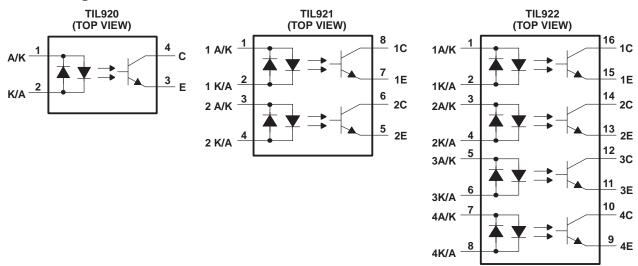


NOTE A: Each pin centerline is located 0,25 (0.010) of its true longitudinal position.

# TIL920, TIL921, TIL922, TIL920A, TIL921A, TIL922A TIL920B, TIL921B, TIL922B SINGLE/DUAL/QUAD CHANNEL OPTOCOUPLERS

SOOS032-D3908, FEBRUARY 1992

### schematic diagrams



### absolute maximum ratings, $T_{\Delta} = 25^{\circ}C$ (unless otherwise noted)

voidio maximum rumigo, ra – zo o (umoso omor moo notou)
Input-to-output voltage (see Note 1) ±7.5 kV peak or dc (±5.3 kV rms)
Collector-emitter voltage (see Note 2)
Emitter-collector voltage
Input diode continuous forward current at (or below) 25°C free-air temperature (see Note 3) ±50 mA
Continuous power dissipation at (or below) 25°C free-air temperature:
Phototransistor (see Note 4)
Input diode plus phototransistor per channel (see Note 5)
Operating free-air temperature range, T <sub>A</sub> –55°C to 100°C
Storage temperature range –55°C to 125°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds

- NOTES: 1. This rating applies for sine-wave operation at 50 or 60 Hz. Service capability is verified by testing in accordance with UL requirements.
  - 2. This value applies when the base-emitter diode is open circuited.
  - 3. Derate linearly to 100°C free-air temperature at the rate of 0.67 mA/°C.
  - 4. Derate linearly to 100°C free-air temperature at the rate of 2 mW/°C.
  - 5. Derate linearly to 100°C free-air temperature at the rate of 2.67 mW/°C.

# electrical characteristics, T<sub>A</sub> = 25°C (unless otherwise noted)

PARAMETER			TEST CONDITIONS		MIN	TYP	MAX	UNIT
V(BR)CEO	Collector-emitte	er breakdown voltage	$I_C = 0.5 \text{ mA},$	IF = 0	35			V
V(BR)ECO	Emitter-collector breakdown voltage		I <sub>C</sub> = 100 μA,	IF = 0	7			V
I <sub>C(off)</sub>	Off-state collector current		V <sub>CE</sub> = 24 V,	I <sub>F</sub> = 0			100	nA
	Current	TIL920, TIL921, TIL922			20%			
CTR <sup>†</sup>	transfer	TIL920A, TIL921A, TIL922A	$I_F = 5 \text{ mA},$	V <sub>CE</sub> = 5 V	50%			
	ratio	TIL920B, TIL921B, TIL922B	1		100%			
∨ <sub>F</sub> †	Input diode static forward voltage		$I_F = 20 \text{ mA}$				1.4	V
V <sub>CE(sat)</sub> †	Collector-emitter saturation voltage		$I_F = 5 \text{ mA},$	I <sub>C</sub> = 1 mA			0.4	V
Cio	Input-to-output capacitance		$V_{in-out} = 0$ ,	f = 1 MHz, See Note 6		1		pF
r <sub>io</sub>	Input-to-output internal resistance		$V_{in-out} = \pm 1 \text{ kV},$	See Note 6		1011		Ω
I <sub>C(on)1</sub> I <sub>C(on)2</sub>	On-state collector current symmetry ratio (see Note 7)		V <sub>CE</sub> = 5 V,	I <sub>F</sub> = 5 mA	1		3	

<sup>&</sup>lt;sup>†</sup> These parameters apply to either direction of the input current.

NOTES: 6. These parameters are measured between all input-diode leads shorted together and all phototransistor leads shorted together.

7. The higher of the two values of  $I_{C(on)}$  generated by the two diodes is taken as  $I_{C(on)1}$ .



# TIL920, TIL921, TIL922, TIL920A, TIL921A, TIL922A TIL920B, TIL921B, TIL922B SINGLE/DUAL/QUAD CHANNEL OPTOCOUPLERS

SOOS032-D3908, FEBRUARY 1992

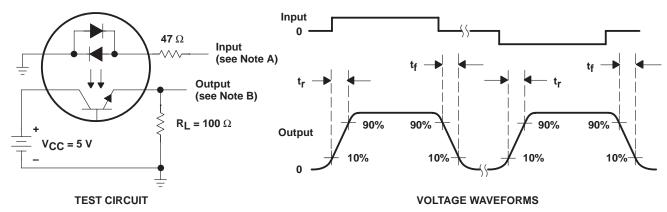
# switching characteristics, T<sub>A</sub> = 25°C

	PARAMETER†	TEST CONDITIONS	TYP	UNIT
t <sub>r</sub>	Rise time	$V_{CC} = 5 \text{ V}$ , $I_{C(on)} = 2 \text{ mA}$ , $R_L = 100 \Omega$ , See Figure 1	6	μs
t <sub>f</sub>	Fall time		6	μο

<sup>†</sup> These parameters apply to either direction of the input current.

#### PARAMETER MEASUREMENT INFORMATION

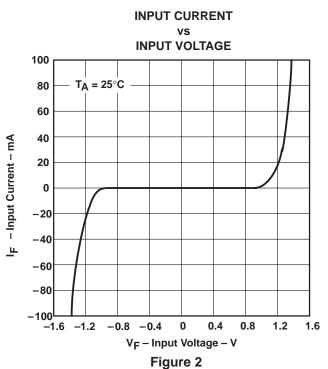
Adjust amplitude of input pulse for  $I_{C(on)} = 2 \text{ mA}$ 



NOTES: A. The input waveform is supplied by a generator with the following characteristics:  $Z_0 = 50~\Omega$ ,  $t_\Gamma \le 15$  ns, duty cycle = 1%. B. The output waveform is monitored on an oscilloscope with the following characteristics:  $t_\Gamma \le 12$  ns,  $R_i \ge 1~M\Omega$ ,  $C_i \le 20~pF$ .

Figure 1. Switching Times

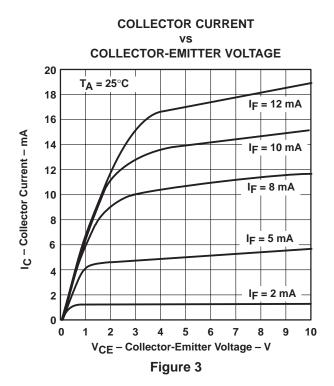
#### TYPICAL CHARACTERISTICS

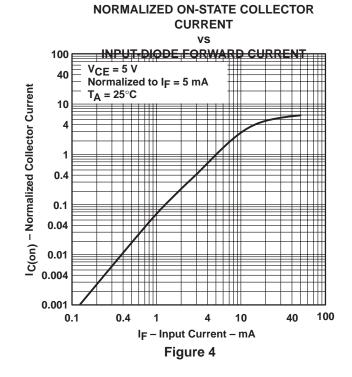




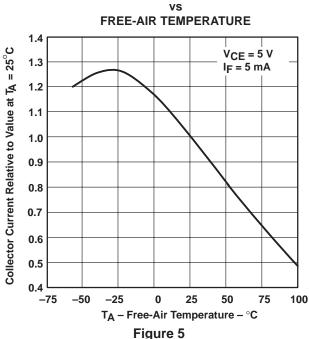
SOOS032-D3908, FEBRUARY 1992

#### TYPICAL CHARACTERISTICS

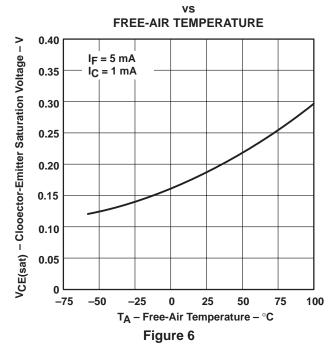




# RELATIVE ON-STATE COLLECTOR CURRENT



### TYPICAL COLLECTOR-EMITTER SATURATION VOLTA





#### **IMPORTANT NOTICE**

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 1998, Texas Instruments Incorporated